Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A method of controlling removal rate uniformity during an electropolishing process in integrated circuit fabrication on a wafer, the method comprising:

applying a stream of electrolyte to the wafer using a nozzle positioned adjacent to the wafer with a gap between the nozzle and the wafer; and

adjusting the gap between the nozzle and the wafer to adjust the removal rate profile of the stream of electrolyte applied by the nozzle.

2. (Original) The method of claim 1, wherein, when the gap is less than a diameter of the stream of electrolyte, the removal rate profile of the stream of electrolyte has a concave shape; and wherein, when the gap is greater than the diameter of the stream of electrolyte, the removal rate profile of the stream of electrolyte has a convex shape.

3. (Original) The method of claim 1, wherein the stream of electrolyte is applied to different radial locations on the wafer, and wherein the gap between the nozzle and the wafer is adjusted based on the radial location of the stream of electrolyte on the wafer.

4. (Original) The method of claim 3, wherein the gap is greater when the stream of electrolyte is applied to a radial location closer to the edge of the wafer than when the stream of electrolyte is applied to a radial location closer to the center of the wafer.

5. (Original) The method of claim 1, wherein the stream of electrolyte is applied from the center of the wafer toward the edge of the wafer, and wherein the gap between the nozzle and the wafer is increased as the stream of electrolyte is applied from the center of the wafer toward the edge of the wafer.

6. (Original) The method of claim 1, wherein the stream of electrolyte is applied from the edge of the wafer toward the center of the wafer, and wherein the gap between the nozzle and the wafer is

decreased as the stream of electrolyte is applied from the edge of the wafer toward the center of the wafer.

7. (Original) A system for controlling removal rate uniformity during an electropolishing process in integrated circuit fabrication on a wafer, the system comprising:

a wafer chuck configured to hold the wafer during the electropolishing process; and

a nozzle configured to apply a stream of electrolyte to the wafer held by the wafer chuck, wherein the nozzle is positioned adjacent to the wafer with a gap between the nozzle and the wafer,

wherein the gap between the nozzle and the wafer is adjusted to adjust the removal rate profile of the stream of electrolyte applied by the nozzle.

8-44. (Canceled)

45. (New) The system of claim 7, wherein the wafer chuck is configured to move up and down to adjust the gap between the nozzle and the wafer, wherein the gap is greater when the nozzle is adjacent to the edge of the wafer than when the nozzle is adjacent to the center of the wafer.

46. (New) The system of claim 45, wherein the wafer chuck is configured to translate from a first position to a second position, wherein in the first position the nozzle is adjacent to the center of the wafer, wherein in the second position the nozzle is adjacent to the edge of the wafer, and wherein wafer chuck is configured to move up to increase the gap as the wafer chuck translates from the first position to the second position.

47. (New) The system of claim 46, further comprising:

a guide rod, wherein the wafer chuck is configured to translate on the guide rod; and

a motor connected to the wafer chuck, wherein the motor is configured to rotate the wafer chuck.

48. (New) The system of claim 45, wherein the wafer chuck is configured to translate from a first position to a second position, wherein in the first position the nozzle is adjacent to the edge of the wafer, wherein in the second position the nozzle is adjacent to the center of the wafer, and

wherein wafer chuck is configured to move down to decrease the gap as the wafer chuck translates from the first position to the second position.

49. (New) The system of claim 48, further comprising:

a guide rod, wherein the wafer chuck is configured to translate on the guide rod; and

a motor connected to the wafer chuck, wherein the motor is configured to rotate the wafer chuck.

50. (New) The system of claim 7, wherein the nozzle is configured to move up and down to adjust the gap between the nozzle and the wafer, wherein the gap is greater when the nozzle is adjacent to the edge of the wafer than when the nozzle is adjacent to the center of the wafer.

51. (New) The system of claim 50, wherein the wafer chuck is configured to translate from a first position to a second position, wherein in the first position the nozzle is adjacent to the center of the wafer, wherein in the second position the nozzle is adjacent to the edge of the wafer, and wherein nozzle is configured to move down to increase the gap as the wafer chuck translates from the first position to the second position.

52. (New) The system of claim 51, further comprising:

a guide rod, wherein the wafer chuck is configured to translate on the guide rod; and

a motor connected to the wafer chuck, wherein the motor is configured to rotate the wafer chuck.

53. (New) The system of claim 50, wherein the wafer chuck is configured to translate from a first position to a second position, wherein in the first position the nozzle is adjacent to the edge of the wafer, wherein in the second position the nozzle is adjacent to the center of the wafer, and wherein nozzle is configured to move up to decrease the gap as the wafer chuck translates from the first position to the second position.

54. (New) The system of claim 53, further comprising:

a guide rod, wherein the wafer chuck is configured to translate on the guide rod; and

a motor connected to the wafer chuck, wherein the motor is configured to rotate the wafer chuck.

55. (New) A system for controlling removal rate uniformity during an electropolishing process in integrated circuit fabrication on a wafer, the system comprising:

a wafer chuck configured to hold the wafer during the electropolishing process; and

a nozzle configured to apply a stream of electrolyte to the wafer held by the wafer chuck, wherein the nozzle is positioned adjacent to the wafer with a gap between the nozzle and the wafer,

wherein the wafer chuck is configured to move up and down to adjust the gap between the nozzle and the wafer to adjust the removal rate profile of the stream of electrolyte applied by the nozzle, wherein the gap is greater when the nozzle is adjacent to the edge of the wafer than when the nozzle is adjacent to the center of the wafer.

56. (New) The system of claim 55, wherein the wafer chuck is configured to translate from a first position to a second position, wherein in the first position the nozzle is adjacent to the center of the wafer, wherein in the second position the nozzle is adjacent to the edge of the wafer, and wherein nozzle is configured to move down to increase the gap as the wafer chuck translates from the first position to the second position.

57. (New) The system of claim 56, further comprising:

a guide rod, wherein the wafer chuck is configured to translate on the guide rod; and

a motor connected to the wafer chuck, wherein the motor is configured to rotate the wafer chuck.